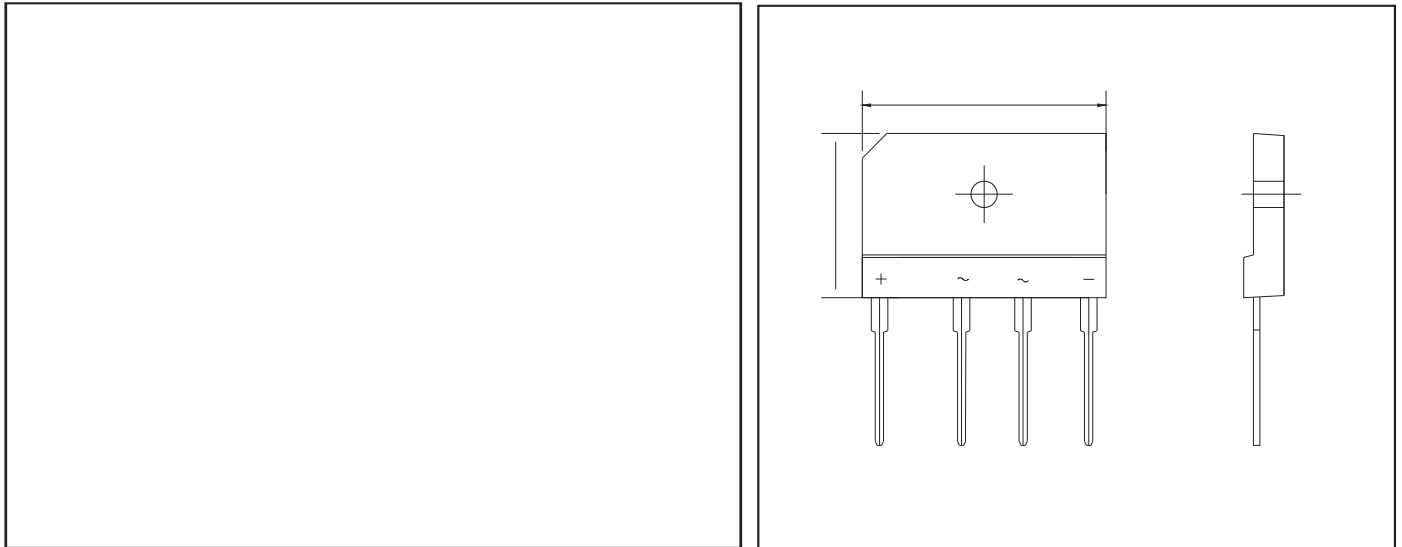


KBJ SILICON BRIDGE RECTIFIER

REVERSE VOLTAGE: 50V ~ 100V CURRENT: 4 A



0.5; 0.8 0.5 7, 1 * 6 1' & + 5 5 & 7 (5, 6 7, & 6

@ 25°C Ambient Temperature (unless otherwise noted) Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate by 20%.

		KBJ 4A	KBJ 4B	KBJ 4D	KBJ 4G	KBJ 4J	KBJ 4K	KBJ 4M	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=100^\circ\text{C}$	$I_{F(AV)}$	4.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	150.0							A
Maximum instantaneous forward voltage at 2.0 A	V_F	1.0							V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	I_R	10.0 1.0							A mA
Typical junction capacitance per element	C_J	45							pF
Typical thermal resistance	R_{JC}	2.2							$^\circ\text{C}/\text{W}$
Operating junction temperature range	T_J	- 55 ---- + 150							$^\circ\text{C}$
Storage temperature range	T_{STG}	- 55 ---- + 150							$^\circ\text{C}$

NOTES: 1. Measured at 1.0mA applied reverse voltage of 4.0V DC

2. Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

